70V9199/099L

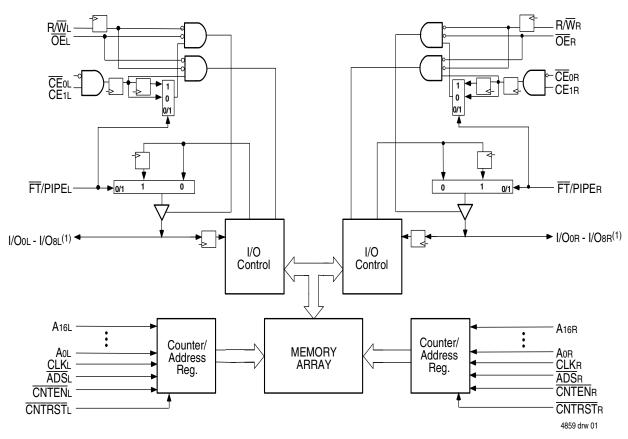
RENESAS HIGH-SPEED 3.3V 128K x9/x8 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 9ns (max.)
 - Industrial: 9ns (max.)
- Low-power operation

 IDT70V9199/099L
 Active: 500mW (typ.)
 - Standby: 1.5mW (typ.)
- Flow-Through or Pipelined output mode on either port via the FT/PIPE pins
- Dual chip enables allow for depth expansion without additional logic

- Counter enable and reset features Full synchronous operation on both ports
- Ans setup to clock and 1ns hold on all control, data, and address inputs
- Data input, address, and control registers
- Fast 9 ns clock to data out in the Pipelined output mode
- Self-timed write allows fast cycle time
- 15ns cycle time, 66 MHz operation in Pipelined output mode
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100-pin Thin Quad Flatpack (TQFP)
- * Green parts available, see ordering information



NOTE: 1. I/Oox - I/O7x for IDT70V9099.

Functional Block Diagram

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JULY 2019

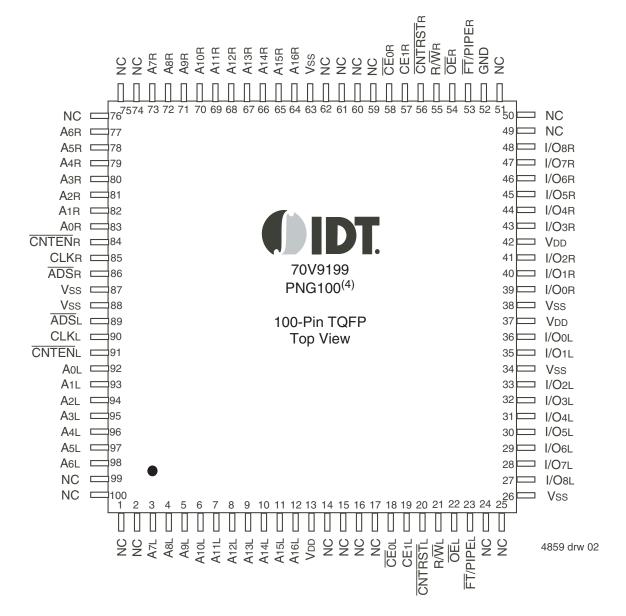
70V9199/099L High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Description:

The IDT70V9199/099 is a high-speed128K x9/x8 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V9199/099 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE} 0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using CMOS high-performance technology, these devices typically operate on only 500mW of power.

Pin Configuration^(1,2,3)

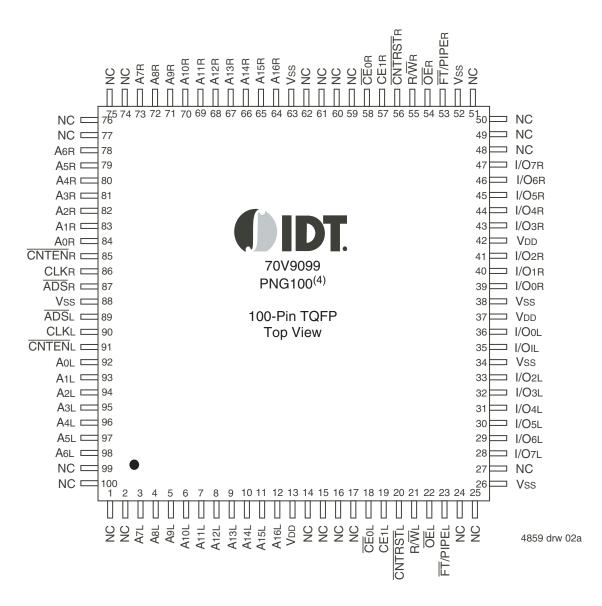


- 1. All VDD pins must be connected to power supply.
- 2. All Vss pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.

70V9199/099L

High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

PinConfiguration^(1,2,3)(con't.)



- 1. All VDD pins must be connected to power supply.
- 2. All Vss pins must be connected to ground.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.

70V9199/099L

High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Pin Names

Left Port	Right Port	Names
CE0L, CE1L	CEOR, CE1R	Chip Enables
R/WL	R/Wr	Read/Write Enable
OEL	ŌĒR	Output Enable
A0L - A16L	AOR - A16R	Address
1/00l - 1/08l ⁽¹⁾	I/O0r - I/O8r ⁽¹⁾	Data Input/Output
CLKL	CLKR	Clock
ADSL	ADSR	Address Strobe Enable
	CNTEN R	Counter Enable
CNTRSTL	CNTRSTR	Counter Reset
FT/PIPEL	FT /PIPER	Flow-Through / Pipeline
	VDD	Power (3.3V)
	Vss	Ground (0V)

NOTE:

1. I/Oox - I/O7x for IDT70V9099.

4859 tbl 01

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	CE 0	CE1	R/W	I/O0-8 ⁽⁴⁾	MODE			
Х	\uparrow	Н	Х	Х	High-Z	Deselected-Power Down			
Х	\uparrow	Х	L	Х	High-Z	gh-Z Deselected-Power Down			
Х	\uparrow	L	Н	L	DATAIN	Write			
L	\uparrow	L	Н	Н	DATAOUT	Read			
Н	Х	L	Н	Х	High-Z	Outputs Disabled			

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{ADS} , \overline{CNTEN} , $\overline{CNTRST} = X$.

3. OE is an asynchronous input signal.

4. I/Oo - I/O7 for IDT70V9099.

External Address	Previous Internal Address	Internal Address Used	CLK	ADS		CNTRST	I/O ⁽³⁾	MODE	
Х	Х	0	\uparrow	Х	Х	L ⁽⁴⁾	D⊮o (0)	Counter Reset to Address 0	
An	Х	An	\uparrow	L ⁽⁴⁾	Х	Н	D⊮o(n)	External Address Loaded into Counter	
An	Ар	Ар	\uparrow	Н	Н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)	
Х	Ар	Ap + 1	\uparrow	Н	L ⁽⁵⁾	Н	D⊮o(p+1)	Counter Enabled—Internal Address generation	
								4859 tbl 03	

Truth Table II—Address Counter Control^(1,2)

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{CE}_0 and \overline{OE} = VIL; CE1 and R/W = VIH.

3. Outputs configured in Flow-Through Output mode; if outputs are in Pipelined mode the data out will be delayed by one cycle.

ADS and CNTRST are independent of all other signals including CEo and CE1.
 The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CEo and CE1.

4859 tbl 02

70V9199/099L

High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature ⁽²⁾	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vdd	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	V
Vih	Input High Voltage	2.0	_	VDD+0.3V ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾		0.8	V

NOTES:

4859 tbl 04

1. VIL \geq -1.5V for pulse width less than 10 ns.

2. VTERM must not exceed VDD +0.3V.

Absolute Maximum Ratings⁽¹⁾

		J	
Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS ⁽³⁾	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
ИГЛ	Junction Temperature	+150	°C
lout	DC Output Current	50	mA
			4859 tbl 06

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

- 2. VTERM must not exceed VDb +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDb + 0.3V.
- 3. Ambient Temperature Under DC Bias. No AC Conditions. Chip deselect.

Capacitance⁽¹⁾

$(TA = +25^{\circ}C, f = 1.0MHz)$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF
				4859 tbl 07

NOTES:

- 2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references Ci/o.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 0.3V)

				70V9199/099L		
Sym	nbol	Parameter	Test Conditions	Min.	Max.	Unit
L	ц	Input Leakage Current ⁽¹⁾	$V_{DD} = 3.6V$, $V_{IN} = 0V$ to V_{DD}	_	5	μA
L	0	Output Leakage Current	\overline{CE} = VIH or CE1 = VIL, VOUT = 0V to VDD	-	5	μA
Vo	DL	Output Low Voltage	IoL = +4mA	_	0.4	V
Vo	ЭН	Output High Voltage	IoH = -4mA	2.4		V

NOTE:

1. At VDD ≤ 2.0V input leakages are undefined.

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4859 tbl 08

4859 tbl 05

^{1.} These parameters are determined by device characterization, but are not production tested.

70V9199/099L

High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

4859 tbl 09

DC Electrical Characteristics Over the Operating <u>Temperature Supply Voltage Range⁽³⁾</u> ($V_{DD} = 3.3V \pm 0.3V$)

						9/099L9 & Ind		9/099L12 I Only	
Symbol	Parameter	Test Condition	Versio	n	Тур. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Мах.	Unit
IDD	Dynamic Operating Current (Both	\overline{CE}_{L} and $\overline{CE}_{R}=$ VIL,	COM'L	L	175	230	150	200	mA
	Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	L	180	240			
ISB1	Standby Current	$\overline{CE}L = \overline{CE}R = VIH$	COM'L	L	40	65	30	50	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	L	50	70			
ISB2	Standby	$\frac{\overline{CE}}{\overline{CE}} = VIL \text{ and }$	COM'L	L	110	145	95	130	mA
	Current (One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L	110	155			
ISB3	Full Standby	Both Ports CEL and	COM'L	L	0.4	2	0.4	2	mA
	$\begin{array}{llllllllllllllllllllllllllllllllllll$		IND	L	0.4	2		-	
ISB4	Full Standby	\overline{CE} "A" $\leq 0.2V$ and	COM'L	L	100	140	90	125	mA
	Current (One Port - CMOS Level Inputs)	$\label{eq:constraints} \begin{array}{l} \overline{\text{CE}}^* \mathbb{B}^* \geq \text{VDD} \cdot 0.2 \text{V}^{(5)} \\ \overline{\text{VIN}} \geq \text{VDD} \cdot 0.2 \text{V or} \\ \overline{\text{VIN}} \leq 0.2 \text{V}, \text{ Active Port,} \\ \overline{\text{Outputs Disabled, } f = \text{fMAX}^{(1)} \end{array}$	IND	L	100	155			

NOTES:

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 90mA (Typ). 5. $\overline{CE}x = VIL$ means $\overline{CE}ox = VIL$ and $CE_{1X} = VIH$

 $\overline{CE}x = VIH$ means $\overline{CE}ox = VIH$ or CE1x = VIL

 $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \leq 0.2 \text{V}$ and $\text{CE}\text{1x} \geq \text{V}\text{DD}$ - 0.2 V $\overline{\text{CE}} x \geq V\text{DD}$ - 0.2V means $\overline{\overline{\text{CE}}} \text{ox} \geq V\text{DD}$ - 0.2V or CE1x $\leq 0.2V$

"X" represents "L" for left port or "R" for right port.

70V9199/099L

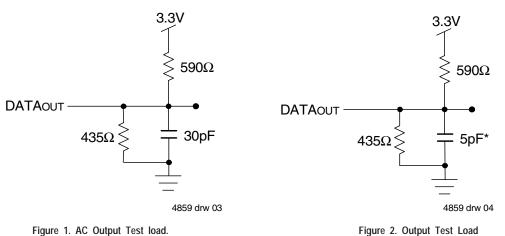
High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

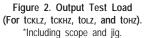
Industrial and Commercial Temperature Ranges

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

4859 tbl 10





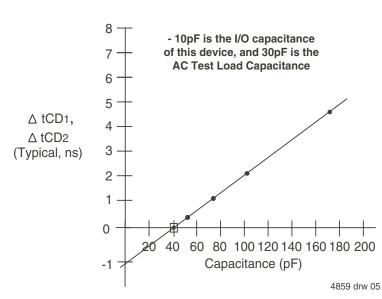


Figure 3. Typical Output Derating (Lumped Capacitive Load).

70V9199/099L

High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

4859 tbl 11

by device

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)⁽³⁾ ($V_{DD} = 3.3V \pm 0.3V$)

		70V919 Com'l	9/099L9 & Ind	70V919 Com		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	25		30		ns
tCYC2	Clock Cycle Time (Pipelined) ⁽²⁾	15		20		ns
tCH1	Clock High Time (Flow-Through) ⁽²⁾	12		12		ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	12		12		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	6		8		ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	6		8		ns
tR	Clock Rise Time		3		3	ns
tF	Clock Fall Time		3	—	3	ns
tsa	Address Setup Time	4		4		ns
tha	Address Hold Time	1		1		ns
tsc	Chip Enable Setup Time	4		4		ns
tнc	Chip Enable Hold Time	1		1		ns
tsw	R/W Setup Time	4		4		ns
tHW	R/W Hold Time	1		1		ns
tsp	Input Data Setup Time	4		4		ns
thd	Input Data Hold Time	1		1		ns
tsad	ADS Setup Time	4		4		ns
thad	ADS Hold Time	1		1		ns
tscn	CNTEN Setup Time	4		4		ns
t HCN	CNTEN Hold Time	1		1		ns
tsrst	CNTRST Setup Time	4		4		ns
thrst	CNTRST Hold Time	1		1		ns
toe	Output Enable to Data Valid		9		12	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2		2		ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾		20		25	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		9	—	12	ns
tDC	Data Output Hold After Clock High	2		2	—	ns
tскнz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2		2		ns
Port-to-Port [Delay	I		•	•	
tcwdd	Write Port Clock High to Read Data Delay		35		40	ns
tccs	Clock-to-Clock Setup Time		15		15	ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed characterization, but is not production tested.

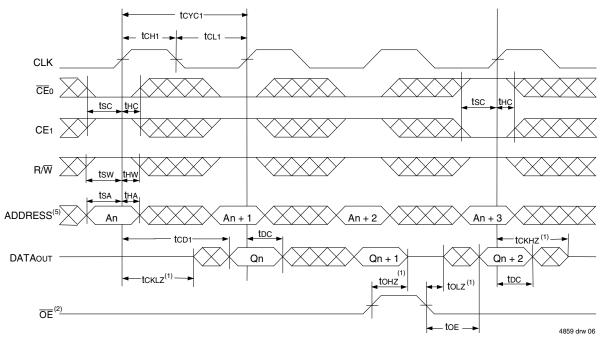
2. The Pipelined output parameters (tcvc2, tcb2) apply to either or both the Left and Right ports when FT/PIPE = VIH. Flow-through parameters (tcvc1, tcb1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER, and FT/PIPEL.

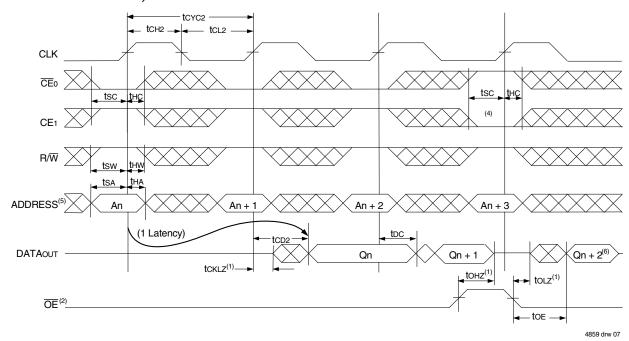
70V9199/099L High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Read Cycle for Flow-Through Output (**FT**/PIPE"x" = VIL)^(3,6)



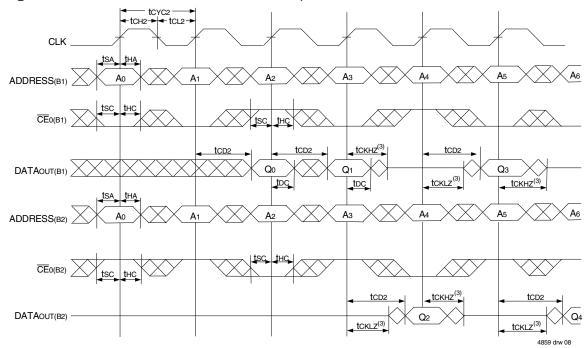
Timing Waveform of Read Cycle for Pipelined Operation $(FT/PIPE"x" = VIH)^{(3,6)}$



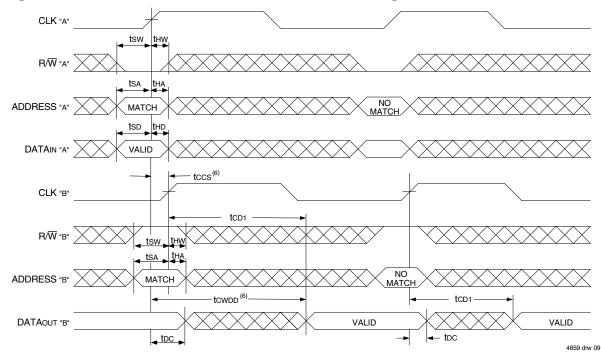
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL$ and $\overline{CNTRST} = VIH$.
- 4. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$ or $CE_1 = V_{IL}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
- are for reference use only. 6. 'X' here denotes Left or Right port. The diagram is with respect to that port.

70V9199/099L High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM Industrial and Commercial Temperature Ranges

Timing Waveform of a Bank Select Pipelined Read^(1,2)



Timing Waveform with Port-to-Port Flow-Through Read^(4,5,7)



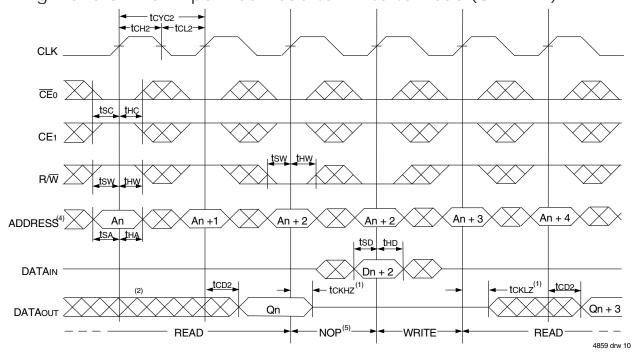
NOTES:

- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9199/099 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{OE}}$ and $\overline{\text{ADS}}$ = VIL; CE1(B1), CE1(B2), R/W and $\overline{\text{CNTRST}}$ = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 and $\overline{ADS} = VIL$; CE1 and $\overline{CNTRST} = VIH$.
- 5. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 6. If tccs < maximum specified, then data from right port READ is not valid until the maximum specified for tcwpp.
- If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

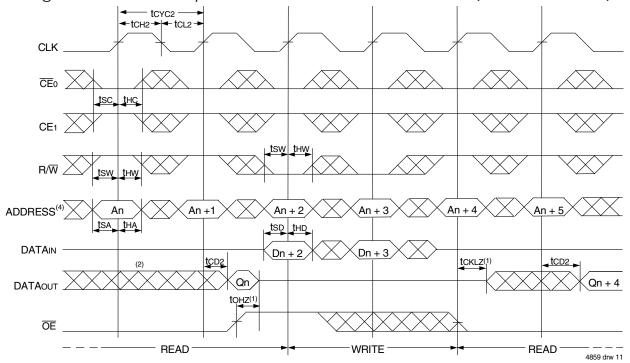
10

70V9199/099L High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM Industrial and Commercial Temperature Ranges

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾



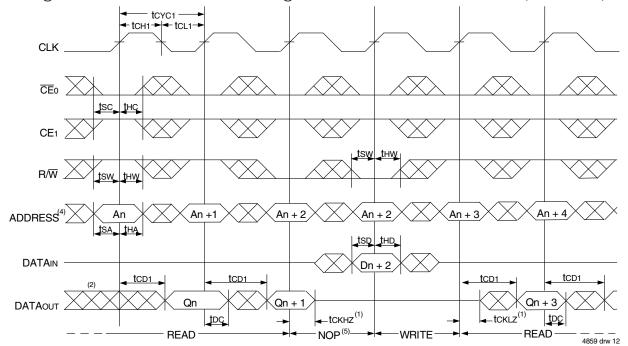
Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽³⁾



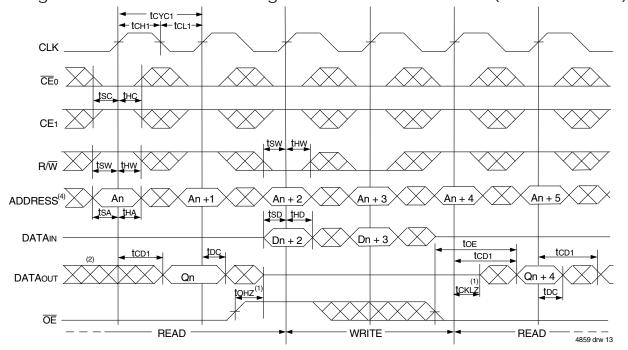
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 and \overline{ADS} = VIL; CE1 and \overline{CNTRST} = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = ViL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.



Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾



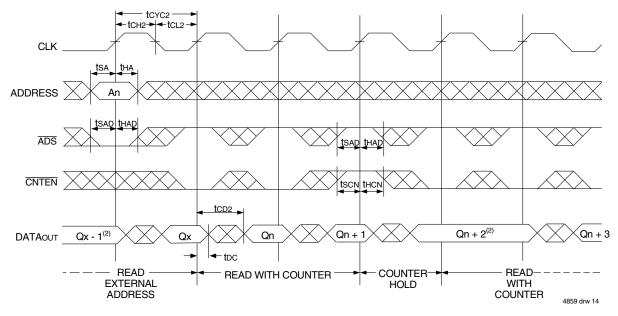
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_0 and $\overline{ADS} = VIL$; CE1 and $\overline{CNTRST} = VIH$. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

70V9199/099L

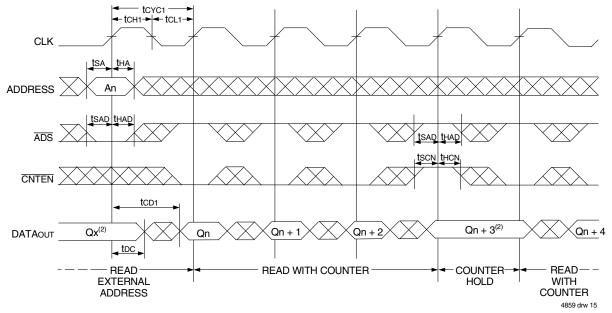
High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾



NOTES:

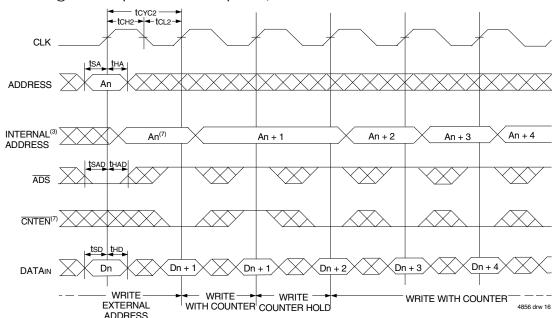
1. \overline{CE}_0 and \overline{OE} = VIL; CE1, R/W, and \overline{CNTRST} = VIH.

2. If there is no address change via ADS = VIL (loading a new address) or CNTEN = VIL (advancing the address), i.e. ADS = VIH and CNTEN = VIH, then the data output remains constant for subsequent clocks.

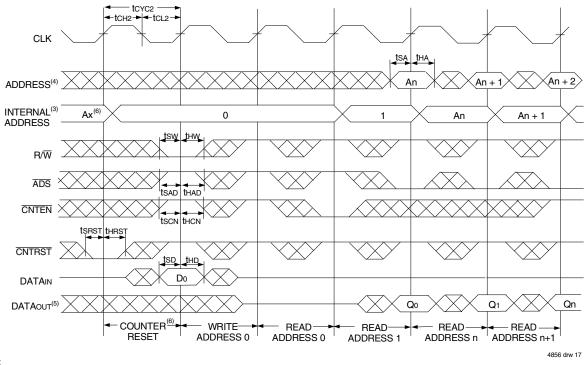
70V9199/099L High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)⁽²⁾



- NOTES:
- 1. \overline{CE}_0 and $R/\overline{W} = V_{IL}$; CE1 and $\overline{CNTRST} = V_{IH}$.
- 2. $\overline{CE}_0 = VIL; CE_1 = VIH.$
- 3. The "Internal Address" is equal to the "External Address" when ADS = ViL and equals the counter output when ADS = ViH.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
 Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- CINTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.

70V9199/099L

High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Functional Description

The IDT70V9199/099 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

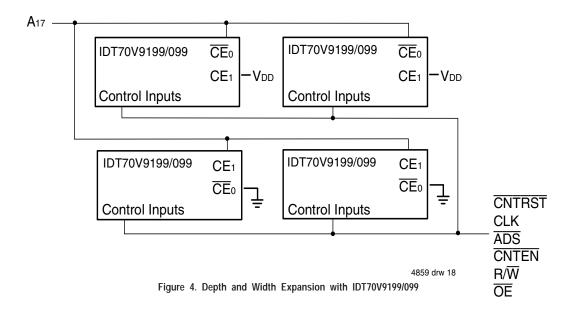
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to staff the operation of the address counters for fast interleaved memory applications.

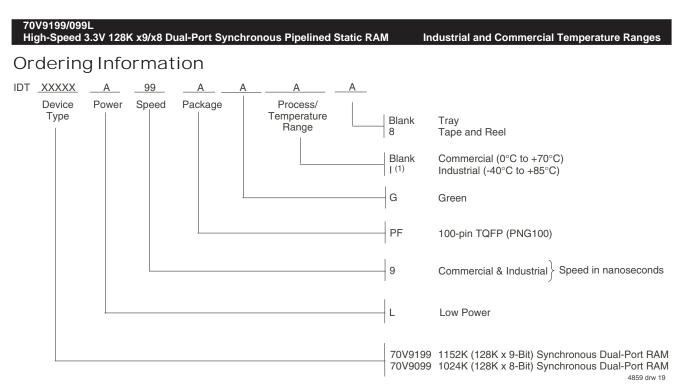
 $\overline{CE}_0 = VIL$ and $CE_1 = VIH$ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9199/099's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{CE}_0 = VIH$ or $CE_1 = VIL$ to reactivate the outputs.

Depth and Width Expansion

The IDT70V9199/099 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the varioius chip enables in order to expand two devices in depth.

The IDT70V9199/099 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 18/16-bit or wider applications.





NOTES:

 Industrial temperature range is available. For specific speeds, packages and powers contact your sales office. LEAD FINISH (SnPb) parts are Obsolete. Product Discontinuation Notice - PDN# SP-17-02 Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

IDT Clock Solution for IDT70V9199/099 Dual-Port

IDT Dual-Port Part Number	Dual-Port I/O Specitications			Dual-Port Clock S	IDT	IDT		
	Voltage	I/O	Input Capacitance	Input Duty Cycle Requirement	Maximum Frequency	Jitter Tolerance	IDT PLL Clock Devices	Non-PLL Clock Devices
70V9199/099	3.3	LVTTL	9pF	40%	100	150ps	IDT2305 IDT2308 IDT2309	FCT3805 FCT3805D/E FCT3807 FCT3807D/E

4859 tbl12

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
9	70V9199L9PFGI	PNG100	TQFP	Ι
	70V9199L9PFGI8	PNG100	TQFP	Ι

Spe (ns		Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
9)	70V9099L9PFG	PNG100	TQFP	С
		70V9099L9PFG8	PNG100	TQFP	С

70V9199/099L High-Speed 3.3V 128K x9/x8 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Datasheet Document History

09/30/99:		Initial Public Release
11/12/99:		Replaced IDT logo
01/10/01:	Page 3	Changed information in Truth Table II
	Page 4	Increased storage temperature parameters
	5	Clarified TA parameter
	Page 5	DC Electrical parameters-changed wording from "open" to "disabled"
	5	Changed ±200mV to 0mV in notes
		Removed Preliminary status
04/09/03:		Consolidate multiple devices into one datasheet
		Changed naming conventions from Vcc to Vpp and from GND to Vss
	Pages 2 & 3	Added date revision to pin configurations
	Page 5	Added junction temperature to Absolute Maximum Ratings Table
	Ū	Added Ambient Temperature footnote
	Pages 1, 6 & 16	Added 6ns speed grade
	Page 6	Added updated DC power numbers to the DC Electrical Characteristics Table
	Page 8	Added 6ns speed AC timing numbers and changed toE to be equal to tcD2 in the AC Electrical
	Ũ	CharacteristicsTable
	Page 16	Added IDT Clock Solution Table
01/10/06:	Page 1	Added green availability to features
	Page 16	Added green indicator to ordering information
02/22/07:	Page 1	Removed 6ns & 7ns speed grades from features
	Page 6	Removed 6ns & 7ns speed grade values from the DC Electrical Characteristics Table
	Page 8	Removed 6ns & 7ns speed grade values from the AC Electrical Characteristics Table
	Page 16	Removed 6ns & 7ns speed grades from ordering information
01/19/09:	Page 16	Removed "IDT" from orderable part number
07/26/10:	Page 8	In order to correct the header notes of the AC Elect Chars Table and align them with the Industrial temp range
		values located in the table, the commercial TA header note has been removed
	Pages 9-12	In order to correct the footnotes of timing diagrams, CNTEN has been removed to reconcile the footnotes with
00/04/40		the CNTEN logic definition found in Truth Table II - Address Counter Control
03/01/18:		Product Discontinuation Notice - PDN# SP-17-02
07/05/10	D. 101(Last time buy expires June 15, 2018
07/25/19:	Page 1 & 16	Deleted obsolete Commercial speed grade12ns in Features and Ordering Information
	Page 2 & 3	Rotated PNG100 TQFP pin configurations to accurately reflect pin 1 orientation
	Page 2 & 3	Updated package code PN100-1 to PNG100
	Page 16	Added Orderable Part Information

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